

Title (en)
INTEGRATED INDUCTIVE CIRCUITS

Title (de)
INTEGRIERTE INDUKTIVE SCHALTKREISE

Title (fr)
CIRCUITS INDUCTEURS INTEGRES

Publication
EP 1203401 A1 20020508 (EN)

Application
EP 00967395 A 20000816

Priority

- US 0040646 W 20000816
- US 58071300 A 20000530
- US 59648600 A 20000619

Abstract (en)
[origin: JP2002134624A] PROBLEM TO BE SOLVED: To form an RF device in a die of the same integrated circuit only by using a CMOS manufacturing process. SOLUTION: An RF (12) circuit may be formed over a triple well that creates two reverse biased junctions (66a and 66c). By adjusting the bias across the junctions, the capacitance (67a and 67b) across the junctions can be reduced, reducing the capacitive coupling from the RF circuits to the substrate (42), improving the self-resonance frequency of inductors (48, 50) and reducing the coupling of unwanted signals and noise from the underlying substrate to the active elements and passive elements such as the capacitors and inductors.

IPC 1-7
H01L 21/02; **H01L 27/092**; **H01L 27/08**

IPC 8 full level
H01L 21/02 (2006.01); **H01L 21/761** (2006.01); **H01L 21/822** (2006.01); **H01L 21/8234** (2006.01); **H01L 23/522** (2006.01); **H01L 27/04** (2006.01); **H01L 27/08** (2006.01); **H01L 27/092** (2006.01)

CPC (source: EP)
H01L 21/761 (2013.01); **H01L 21/823481** (2013.01); **H01L 23/5227** (2013.01); **H01L 27/08** (2013.01); **H01L 27/0928** (2013.01); **H01L 28/10** (2013.01); **H01L 2924/0002** (2013.01); **H01L 2924/3011** (2013.01)

Citation (search report)
See references of WO 0193317A1

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AU 7760200 A 20011211; EP 1203401 A1 20020508; JP 2002134624 A 20020510; TW 492195 B 20020621

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